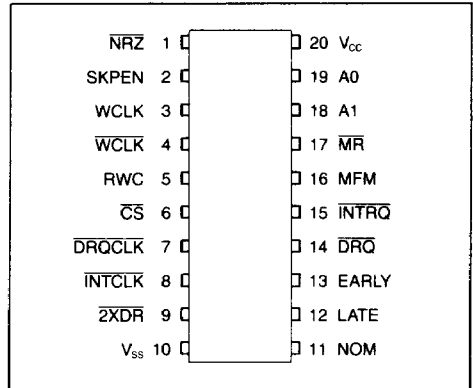# STANDARD MICROSYSTEMS CORPORATION

Hard Disk Improved MFM Generator

FEATURES

☐ Single + 5 Volt Power Supply
☐ Write Precompensation
☐ Address Mark Generation
☐ 5 Mbit Data Rate
☐ Converts NRZ to MFM
☐ 20 Pin DIP
☐ n-Channel COPLAMOS® Silicon Gate Technology

PIN CONFIGURATION

| Pin	Name		Pin	Name
1	$\overline{NRZ}$		20	V_{cc}
2	SKPEN		19	A0
3	WCLK		18	A1
4	$\overline{WCLK}$		17	$\overline{MR}$
5	RWC		16	MFM
6	$\overline{CS}$		15	$\overline{INTRQ}$
7	$\overline{DRQCLK}$		14	$\overline{DRQ}$
8	$\overline{INTCLK}$		13	EARLY
9	$\overline{2XDR}$		12	LATE
10	V_{ss}		11	NOM

GENERAL DESCRIPTION

The HDC 1100-12 "improved" MFM Generator converts serial NRZ data into an MFM (Modified Frequency Modulated) data stream. The MFM signal may be used to record information on a Winchester Disk.

In addition, the HDC 1100-12 generates Write Precompensation signals required to compensate for bit shift effects on the recording medium.

The HDC 1100-12 has the ability to delete clock pulses in the outgoing data stream in order to record Address Marks.

SECTION VI

MFM GENERATOR

INTERRUPT CONTROLLER
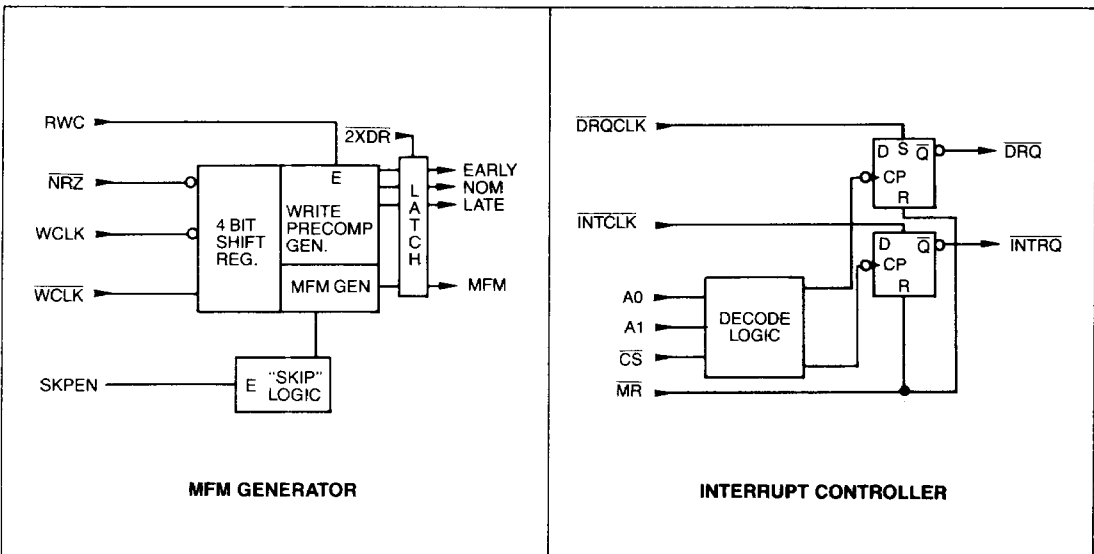
DESCRIPTION OF PIN FUNCTIONS

PIN NUMBER	SYMBOL	NAME	FUNCTION
1	NRZ	NON-RETURN-TO ZERO	NRZ data input that is strobed into the MFM generator by WCLK (↓).
2	SKPEN	SKIP ENABLE	This input arms the SKIP logic for recording Address Marks when set to a logic 1.
3	WCLK	WRITE CLOCK	Complimentary clock inputs. NRZ data is clocked into the MFM Generator on the high-to-low transition of WCLK (pin 3).
4	WCLK	WRITE CLOCK	
5	RWC	REDUCED WRITE CURRENT	This signal when high, enables EARLY, LATE and NOM outputs.
9	2 x DR	2 TIMES DATA RATE	This input is used to latch EARLY, LATE, NOM and MFM outputs.
10	V$_{ss}$	V$_{ss}$	Ground.
11	NOM	NOMINAL	Output signal from the Write Precompensation Logic used to signify that data is to be written nominal.
12	LATE	LATE	Output signal from the Write Precompensation Logic used to signify that data is to be shifted LATE before writing.
13	EARLY	EARLY	Output signal from the Write Precompensation Logic used to signify that data is to be shifted EARLY before writing.
16	MFM	MFM DATA	This output contains the MFM encoded data derived from the NRZ (pin 1) line.
6	CS	CHIP SELECT	Low input signal used to enable the Address decode logic.
8	INTCLK	INTERRUPT REQUEST CLOCK	A high-to-low transition on this line will latch the INTRQ (pin 15) at a logic 0.
7	DRQCLK	DATA REQUEST CLOCK	A high-to-low transition on this line will latch the DRQ (pin 14) at a logic 0.
15	INTRQ	INTERRUPT REQUEST	This output is latched at a logic 0 when INTCLK (pin 8) makes a high-to-low transition while the decode logic is disabled.
14	DRQ	DATA REQUEST	This output is latched at a logic 0 when DRQCLK (pin 7) makes a high-to-low transition while the decode logic is disabled.
17	MR	MASTER RESET	A low level on this line causes DRQ and INTRQ to set at a logic 1.
18, 19	A$_0$, A$_1$	ADDRESS 1, 0	When CS is low and the address lines are high, INTRQ is cleared; if the address lines are low then DRQ gets cleared. (i.e. set at a logic 1).
20	V$_{cc}$	V$_{cc}$	+ 5V power supply input.

OPERATION

The HDC 1100-12 is divided into two sections: MFM Generator and Interrupt Logic. The MFM Generator converts NRZ data into MFM data and provides Write Precompensation signals. The Interrupt Logic may be used to generate Interrupt signals. The two sections of the device are isolated and have no common input or output signals.

Prior to entering data, the SKPEN line must be set to a logic 0 to enable only clocks in the data stream. Data is entered on the NRZ line and strobed on the high-to-low transition of WCLK. The encoded NRZ data appears on the MFM (pin 16) output lagging by one clock cycle.

Write Precompensation signals EARLY, LATE, and NOM are generated as each data or clock pulse becomes available at the input when RWC is logic 1.

The SKPEN signal is used to record a unique data/clock pattern as an Address Mark, using A1 data with 0A clock. This pattern is used for synchronization prior to data or ID fields that are read from the disk.

When the SKPEN signal is set to a logic 1, the internal skip

logic is enabled. As long as zeroes are being shifted into the NRZ line, the device generates normal MFM data. On receipt of the first non-zero bit (typically the MSB of the A1 16) the skip logic begins to count WCLK cycles. When the MFM generator tries to produce a clock between data bits 2 and 3, the skip logic disables the MFM generator during that time. The result for A1$_{16}$ data is a clock pattern of 0A$_{16}$ instead of OE$_{16}$. Although other data patterns may be used,

MR	A$_1$	A$_0$	CS	DRQ	INTRQ
0	X	X	X	H	H
1	X	X	1	Q$_N$	Q$_N$
1	0	0	0	H	Q$_N$
1	1	1	0	Q$_N$	H
1	1	0	0	Q$_N$	Q$_N$
1	0	1	0	Q$_N$	Q$_N$

X = Don't care   Q$_N$ = remains at previous state

INTERRUPT REQUEST LOGIC TABLE

the MSB of the pattern must be a 1 (80_{16} or higher) in order to enable the skip logic at the proper time. After the skip logic has performed, it then disables itself and MFM data is recorded normally starting with the succeeding byte. To re-enable the skip logic again, the SKPEN line must be strobed.

The Interrupt Logic is used to clear Data Requests ($\overline{DRQ}$) and Interrupt Requests (INTRQ) by selecting $\overline{CS}$ (pin 6) in combination with A0 and A1. The $\overline{MR}$ (Master Reset) signal is used to clear both $\overline{DRQ}$ and $\overline{INTRQ}$ simultaneously. $\overline{DRQ}$ and $\overline{INTRQ}$ can be set to a logic 0 only by a low level or $\overline{DRQCLK}$ and $\overline{INTCLK}$ respectively. The signal will remain at a logic 0 until cleared by a $\overline{MR}$ or proper address selection via $\overline{CS}$, A1 and A0.

LAST DATA SENT		SENDING	TO BE SENT NEXT	EARLY	LATE	NOM
X	1	1	0	H	L	L
X	0	1	1	L	H	L
0	0	0	1	H	L	L
1	0	0	0	L	H	L
ANY OTHER PATTERN				L	L	H

WRITE PRECOMPENSATION LOGIC TABLE

MAXIMUM GUARANTEED RATINGS*

Operating Temperature Range .... 0°C to +50°C
Storage Temperature Range .... −55° to +150°C
Lead Temperature (soldering, 10 sec.) .... +300°C
Positive Voltage on any I/O Pin, with respect to ground .... +7.0V
Negative Voltage on any I/O Pin, with respect to ground .... −0.2V
Power Dissipation .... 1.0 watt

*Stresses above those listed may cause permanent damage to the device. This is a stress rating only and fu...
device at these or at any other condition above those indicated in the operational sections of this specification is...

DC ELECTRICAL CHARACTERISTICS: T_A = 0°C to 50°C; V_{CC} = +5V ± 10%; V_{SS} = 0V
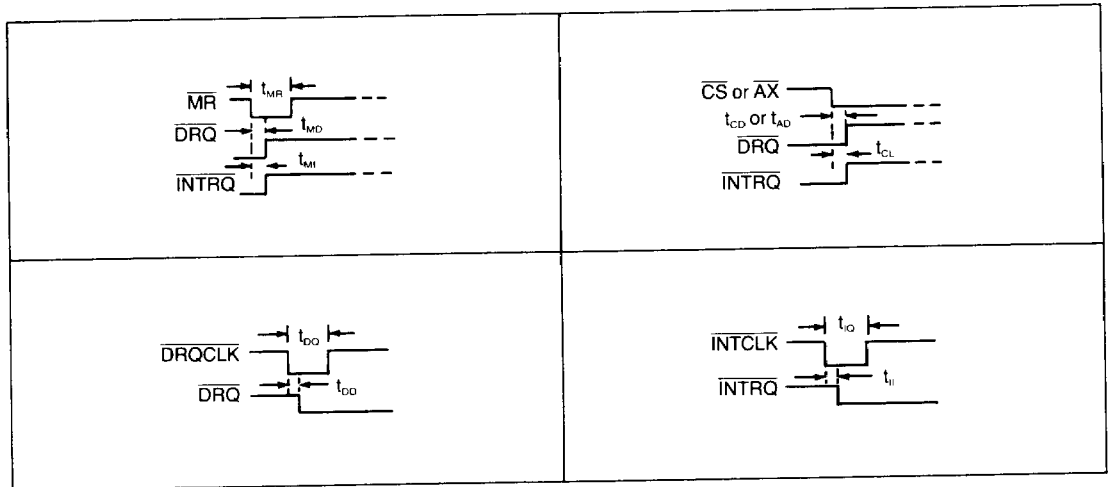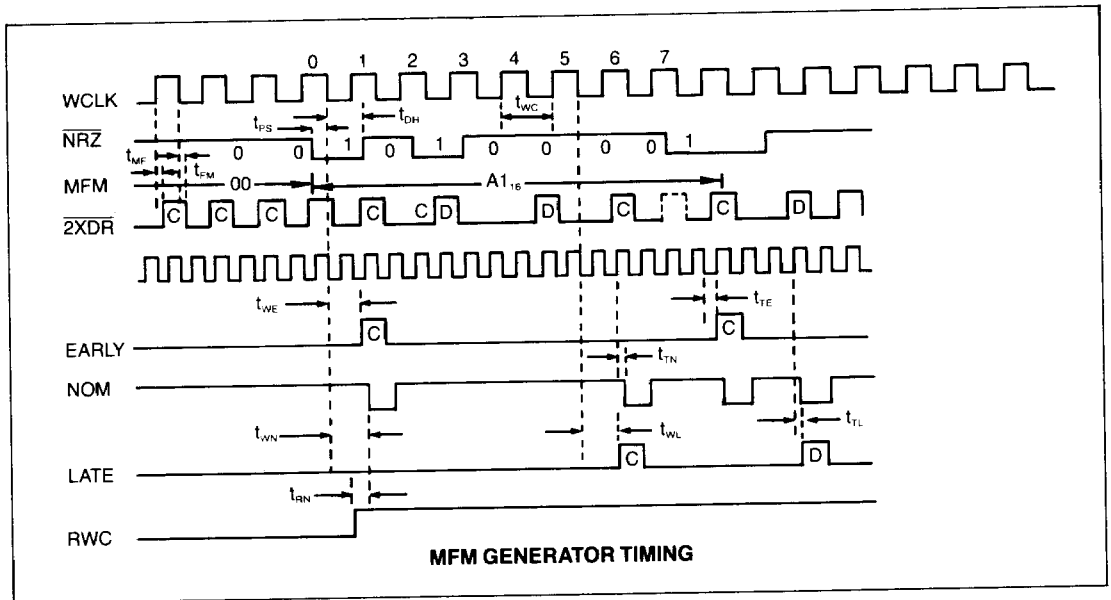
SYMBOL	PARAMETER	MIN	TYP[1]	MAX	UNIT	CONDITION
V_{IL}	Input Low Voltage	−0.2		0.8	V	
V_{IH}	Input High Voltage	2.4			V	
V_{OL}	Output Low Voltage			0.4	V	I_{OL} = 3.2 mA
V_{OH}	Output High Voltage	2.4			V	I_{OH} = −200μA
V_{CC}	Supply Voltage	4.5	5.0	5.5	V	
I_{CC}	Supply Current			100	mA	All Outputs Open

AC ELECTRICAL CHARACTERISTICS: T_A = 0°C to 50°C; V_{CC} = +5V ± 10%; V_{SS} = 0V

SYMBOL	PARAMETER	MIN	TYP[1]	MAX	UNIT	CONDITION
t_{FR}	WCLK FREQUENCY			5.25	MHZ	
t_{DS}	Data Setup w.r.t. ↓ WCLK	10			nsec	
t_{DH}	Data hold w.r.t. ↓ WCLK	25			nsec	
t_{MF}	↑ WCLK to ↑MFM delay			210	nsec	Pin 1 LOW
t_{FM}	↓ WCLK to ↓ MFM delay			230	nsec	Pin 1 LOW
t_{WN}	Data delay to NOM from ↓ WCLK			240	nsec	
t_{WE}	Data delay to EARLY from ↓ WCLK			230	nsec	
t_{WL}	Data delay to LATE from ↓ WCLK			230	nsec	
t_{MR}	Master reset pulse width	50			nsec	
t_{MD}	↓ MR to ↑ $\overline{DRQ}$			150	nsec	
t_{MI}	↓MR to ↑ $\overline{INTRQ}$			150	nsec	
t_{DD}	$\overline{DRQCLK}$ pulse width	50			nsec	
t_{IC}	$\overline{INTCLK}$ pulse width	50			nsec	
t_{DD}	↓ $\overline{DRQCLK}$ to $\overline{DRQ}$			120	nsec	
t_{II}	↓ $\overline{INTCLK}$ to $\overline{INTRQ}$			120	nsec	
t_{AD}	↓ AX to ↑ $\overline{DRQ}$			145	nsec	
t_{AI}	↑ AX to ↑ $\overline{INTRQ}$			160	nsec	
t_{CD}	↓ $\overline{CS}$ to ↑ $\overline{DRQ}$			145	nsec	
t_{CI}	↓ $\overline{CS}$ to ↑ $\overline{INTRQ}$			180	nsec	
t_{RN}	↑ RWC to . NOM			145	nsec	
t_{TE}	↓ $\overline{2XDR}$ to ' EARLY			75	nsec	
t_{TN}	↓ $\overline{2XDR}$ to ↑ NOM			75	nsec	
t_{TL}	↓ $\overline{2XDR}$ to ↑ LATE			75	nsec	

Notes: 1. Typical Values are for T_A = 25°C and V_{CC} = +5.0V.

MFM GENERATOR TIMING